



#### 80V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> Tc = +25°C
80V	7.8mΩ @ V <sub>GS</sub> = 10V	92A

### **Description and Applications**

This new generation MOSFET is designed to minimize  $R_{DS(ON)}$  yet maintain superior switching performance. This device is ideal for use in power management and load switches.

- DC-DC converters
- Load switches

### **Features**

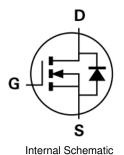
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production —
   Ensures More Reliable and Robust End Application
- High-Conversion Efficiency
- Low RDS(ON) Minimizes On-State Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An automotive-compliant part is available under separate datasheet (<u>DMTH8008SPSQ</u>)

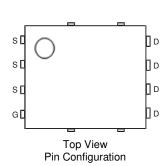
#### **Mechanical Data**

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 <a>3</a>
- Weight: 0.097 grams (Approximate)

Site 1:





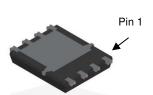


Site 2:

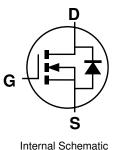
PowerDI5060-8/SWP (Type UX)

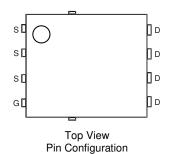


Top View



**Bottom View** 





Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



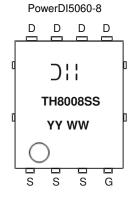
### Ordering Information (Note 4)

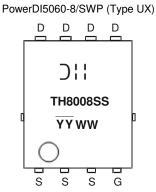
Part Number	Package	Packing		
Part Number	Package	Qty.	Carrier	
DMTH8008SPS-13	PowerDI5060-8	2500	Tape & Reel	
DIVITH00083F3-13	PowerDI5060-8/SWP (Type UX)	2500	Tape & Reel	

Note:

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**





TH8008SS = Product Type Marking Code
YYWW or YYWW = Date Code Marking
YY or YY = Year (ex: 23 = 2023)
WW = Week (01 to 53)

# Maximum Ratings (@Tc = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	80	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current, $V_{GS} = 10V$ (Note 5) Steady $T_{C} = +25^{\circ}C$ State $T_{C} = +100^{\circ}C$			lo	92 65	Α
Maximum Continuous Body Diode Forward Current (Note 5)			ls	83	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	360	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			lsм	360	Α
Avalanche Current, L = 0.1mH (Note 6)			las	40	Α
Avalanche Energy, L = 0.1mH (Note 6)			Eas	80	mJ

## Thermal Characteristics (@Tc = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 7)	T <sub>A</sub> = +25°C	PD	1.6	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	Reja	95	°C/W
Total Power Dissipation (Note 8)	T <sub>A</sub> = +25°C	PD	3.4	W
Thermal Resistance, Junction to Ambient (Note 8)	Steady State	Reja	44	°C/W
Total Power Dissipation (Note 5)	T <sub>C</sub> = +25°C	P <sub>D</sub>	100	W
Thermal Resistance, Junction to Case (Note 5)		Rejc	1.5	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Notes:

- ${\bf 5.}\ Thermal\ resistance\ from\ junction\ to\ soldering\ point\ (on\ the\ exposed\ drain\ pad).$
- 6.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_{J} = +25^{\circ}C$ .
- 7. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
- 8. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.



# **Electrical Characteristics** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	80	_	_	V	VGS = 0V, ID = 1mA	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	_	4	V	$V_{DS} = V_{GS}$ , $I_D = 1mA$	
Static Drain-Source On-Resistance	D	_	6.5	7.8	mΩ	$V_{GS} = 10V, I_D = 14A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	7.8	11	11177	$V_{GS} = 6V, I_D = 12A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.8	1.2	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 14A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	_	1950	_			
Output Capacitance	Coss	_	826	_	рF	$V_{DS} = 40V$ , $V_{GS} = 0V$ f = 1MHz	
Reverse Transfer Capacitance	Crss	_	56	_			
Gate Resistance	Rg	_	1.7	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 6V)	Qg	_	23	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	34	_	nC	V <sub>DS</sub> = 40V, I <sub>D</sub> = 14A	
Gate-Source Charge	Qgs	_	6	_	IIC		
Gate-Drain Charge	$Q_{gd}$	_	12	_			
Turn-On Delay Time	tD(ON)	_	8	_			
Turn-On Rise Time	tr	_	15	_		$\begin{split} V_{DD} &= 40 V, \ V_{GS} = 10 V \\ I_D &= 14 A, \ R_g = 6 \Omega \end{split}$	
Turn-Off Delay Time	tD(OFF)	_	29	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	21	_			
Body Diode Reverse Recovery Time	trr	_	43	_	ns	I 144 dl/dt 1004/	
Body Diode Reverse Recovery Charge	Qrr		49		nC	Is = 14A, dl/dt = 100A/µs	

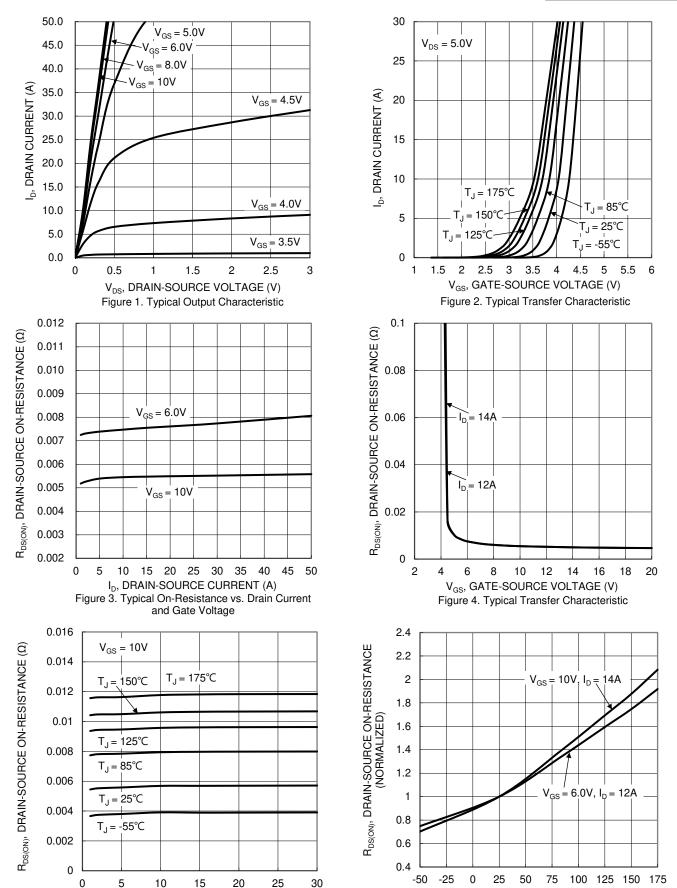
Notes:

<sup>9.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>10.</sup> Guaranteed by design. Not subject to product testing.







I<sub>D</sub>, DRAIN CURRENT (A)

Figure 5. Typical On-Resistance vs. Drain Current

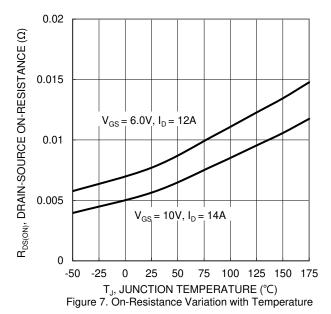
and Temperature

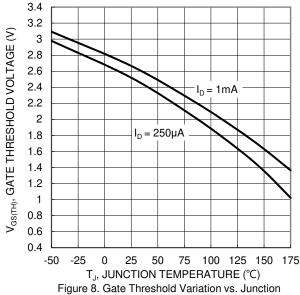
T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Figure 6. On-Resistance Variation with

Temperature

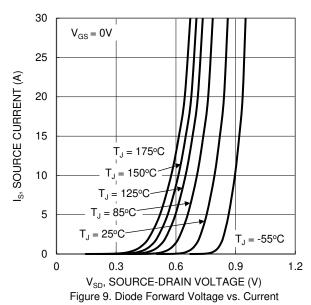


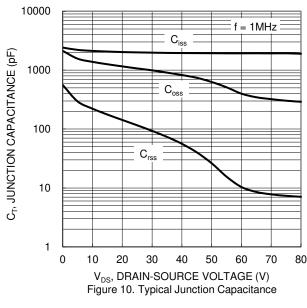


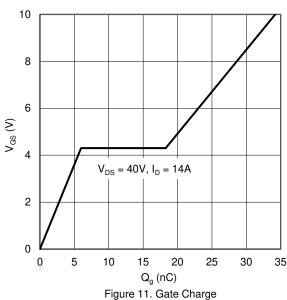


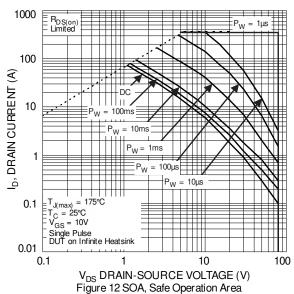


Temperature











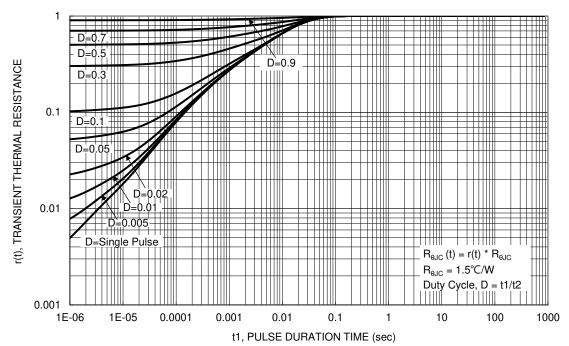


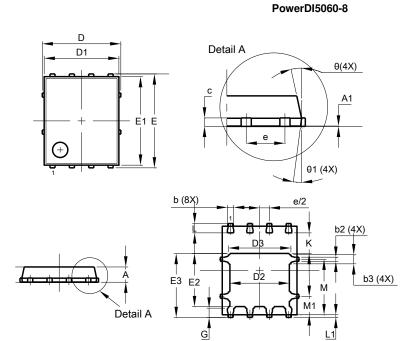
Figure 13. Transient Thermal Resistance



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

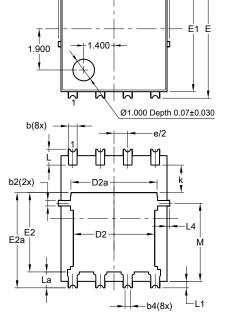
Site 1:

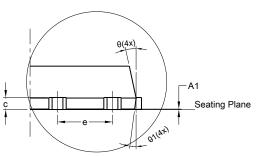


PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0.00	0.05	_	
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
C D	0.230	0.330	0.277	
_		5.15 BSC		
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
Е	(	6.15 BSC	;	
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е		1.27 BSC		
G	0.51	0.71	0.61	
K	0.51	-	-	
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
М	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
Θ	10°	12°	11°	
Θ1	6°	8°	7°	
All Dimensions in mm				

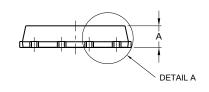
Site 2:

#### PowerDI5060-8/SWP (Type UX)





DETAIL A



PowerDI5060-8/SWP				
(Type UX)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05		
b	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4	(	).25REF		
С	0.230	0.330	0.277	
D	5	.15 BS0	$\sim$	
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
E	6	.40 BS0		
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a	4.195	4.595	4.395	
е		.27BSC		
k	1.05			
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0.050REF			
L4	0.025	0.225	0.125	
М	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

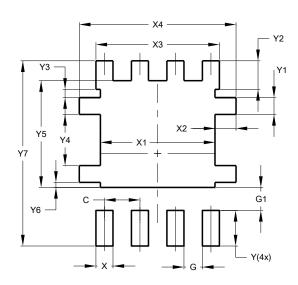


### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

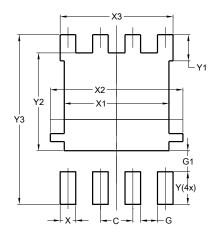
#### PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Υ	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
<b>Y</b> 7	6.610

Site 2:

#### PowerDI5060-8/SWP (Type UX)



Dimensions	Value
Dilliciisions	(in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
Х3	4.420
Υ	1.270
<b>Y</b> 1	1.020
Y2	3.810
Y3	6.610



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